

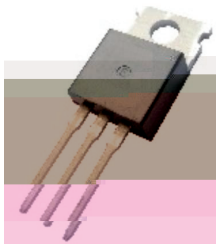
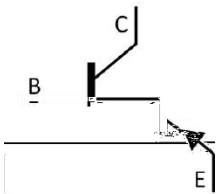
/ Descriptions

Silicon PNP transistor in a TO-220 Plastic Package.

/ Features 324.4P523n12 0.2116 0.001180.0033n12 0554 60846.24 18ref62.0 6084638.00fB/TT81 Tf

Complementary pair with 2SC2344.

High voltage switching, AF power amplifier, 100W output predriver applications.



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

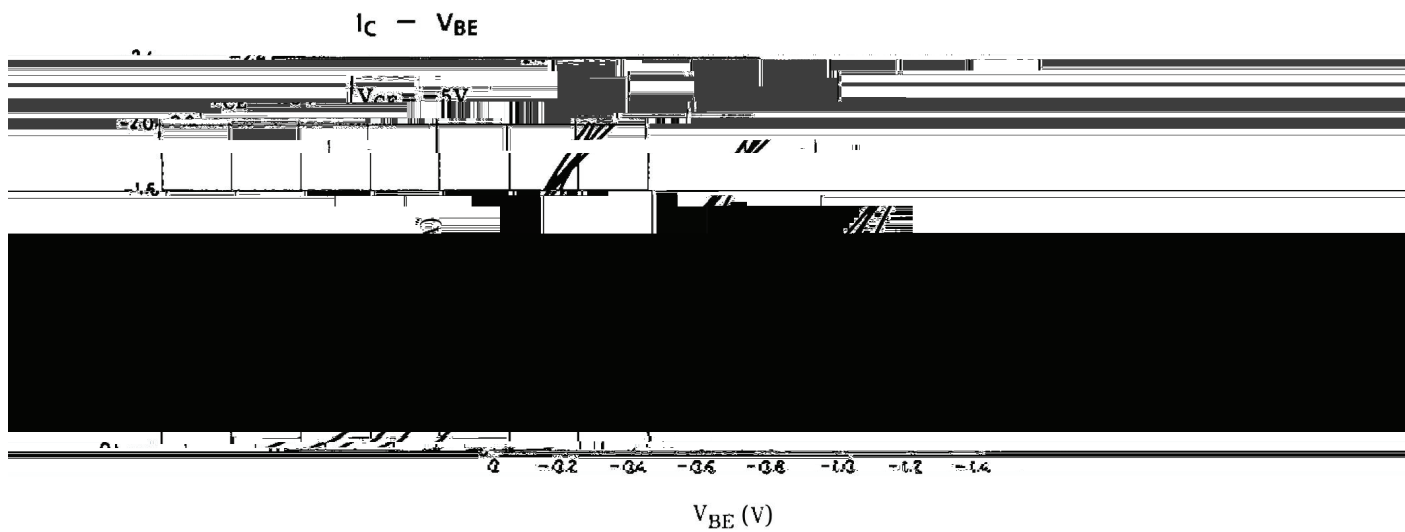
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	-3.0	A
Collector Power Dissipation	P_C	2.0	W
	$P_C(T_C=25)$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CBO}	$I_C=-1.0mA$ $I_E=0$	-180			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-160			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10mA$ $I_C=0$	-6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-120V$ $I_E=0$			-10	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-4.0V$ $I_C=0$			-10	A
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-300mA$	60		200	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-50mA$		-0.5		V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-5.0V$ $I_C=-10mA$		-1.5		V
Transition Frequency	f_T	$V_{CE}=-10V$ $I_C=-50mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$		30		pF
Turn-On Time	t_{on}	$-10I_{B1}=10I_{B2}=-I_C=-0.5A$		0.29		s
Turn-Off Time	t_{off}			0.19		s
Storage Time	t_{stg}			0.48		s

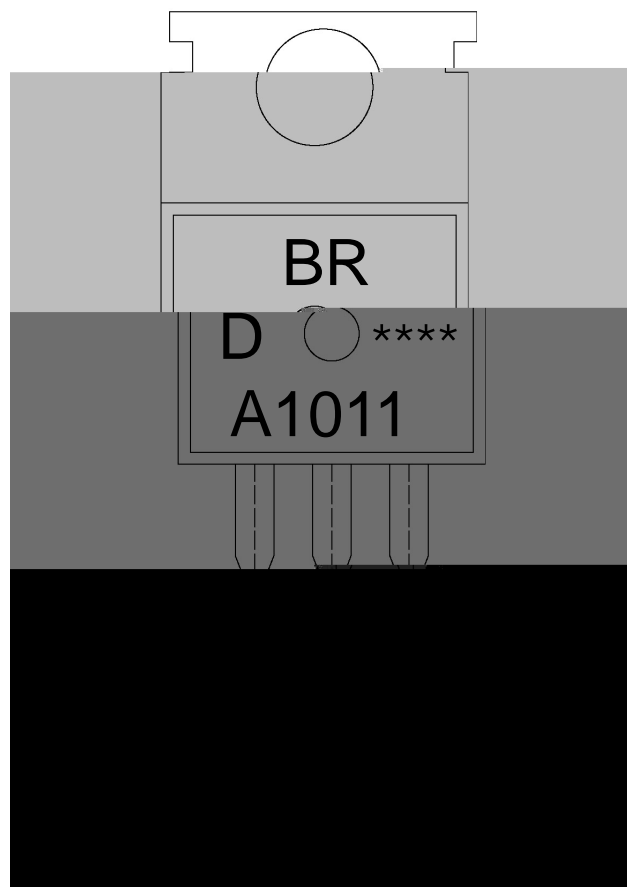
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1011

D h_{FE}

Note:

BR: Company Code

A1011: Product Type.

D: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

